

Silicon PNP Power Transistors

2N5193 2N5194 2N5195

DESCRIPTION

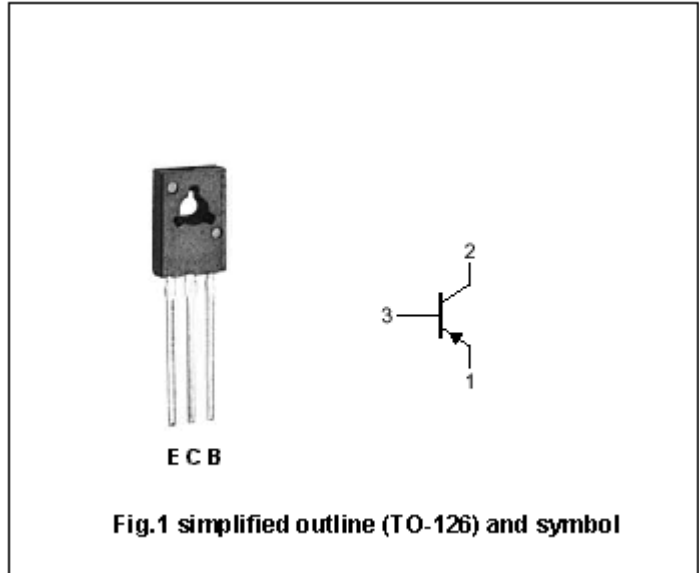
- With TO-126 package
- Complement to type 2N5190,2N5191,2N5192
- Excellent safe operating area

APPLICATIONS

- For use in medium power linear and switching applications

PINNING

PIN	DESCRIPTION
1	Emitter
2	Collector;connected to mounting base
3	Base



Absolute maximum ratings(Ta=25)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CB0}	Collector-base voltage	2N5193	-40	V
		2N5194	-60	
		2N5195	-80	
V _{CEO}	Collector-emitter voltage	2N5193	-40	V
		2N5194	-60	
		2N5195	-80	
V _{EBO}	Emitter-base voltage	Open collector	-5	V
I _C	Collector current		-4	A
I _{CM}	Collector current-Peak		-7	A
I _B	Base current		-1	A
P _D	Total power dissipation	T _C =25	40	W
T _j	Junction temperature		150	
T _{stg}	Storage temperature		-65~150	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	3.12	/W

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CHARACTERISTICS

T_j=25 unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V _{CEO}	Collector-emitter sustaining voltage	2N5193	I _C =-0.1A; I _B =0			V
		2N5194				
		2N5195				
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =-1.5A; I _B =-0.15A			-0.6	V
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =-4A; I _B =-1A			-1.2	V
V _{BE}	Emitter-base on voltage	I _C =-1.5A; V _{CE} =-2V			-1.2	V
I _{CEO}	Collector cut-off current	2N5193				mA
		2N5194				
		2N5195				
I _{CBO}	Collector cut-off current	2N5193				mA
		2N5194				
		2N5195				
I _{CEX}	Collector cut-off current	2N5193				mA
		2N5194				
		2N5195				
I _{EBO}	Emitter cut-off current	V _{EB} =-5V; I _C =0			-1.0	mA
h _{FE-1}	DC current gain	2N5193	I _C =-1.5A; V _{CE} =-2V			
		2N5194				
		2N5195				
h _{FE-2}	DC current gain	2N5193	I _C =-4A; V _{CE} =-2V			
		2N5194				
		2N5195				
f _T	Transition frequency	I _C =-1A; V _{CE} =-10V; f=1MHz	2			MHz

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PACKAGE OUTLINE

